RQ3G100GN

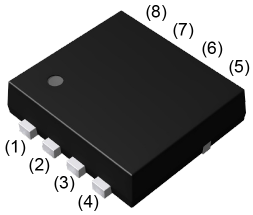
Nch 40V 10A Power MOSFET

Datasheet

V_{DSS}	40V
$R_{DS(on)}$(Max.)	14.3mΩ
I_D	±10A
P_D	2W

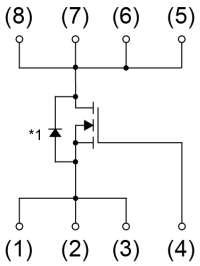
●Outline

HSMT8



●Inner circuit

(1) Source
(2) Source
(3) Source
(4) Gate
(5) Drain
(6) Drain
(7) Drain
(8) Drain
*1 Body Diode



●Features

1) Low on - resistance.
2) High Power Package (HSMT8).
3) Pb-free lead plating ; RoHS compliant.
4) Halogen Free.

●Application

Switching

●Packaging specifications

Type	Packing	Embossed Tape
	Reel size (mm)	330
	Tape width (mm)	12
	Basic ordering unit (pcs)	3000
	Taping code	TB
	Marking	G100GN

●Absolute maximum ratings (T_a = 25°C)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	40	V
Continuous drain current	I_D	±10	A
Pulsed drain current	$I_{D,pulse}$ *1	±40	A
Gate - Source voltage	V_{GSS}	±20	V
Avalanche energy, single pulse	E_{AS} *2	15.6	mJ
Avalanche current	I_{AS} *2	10	A
Power dissipation	P_D *3	2	W
Junction temperature	T_j	150	℃
Range of storage temperature	T_{stg}	-55 to +150	℃

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●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - ambient	R_{thJA} *3	-	62.5	-	℃/W

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 1mA	40	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	I_D = 1mA referenced to 25℃	-	26.2	-	mV/℃
Zero gate voltage drain current	I_{DSS}	V_{DS} = 40V, V_{GS} = 0V	-	-	1	μA
Gate - Source leakage current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V	-	-	±100	nA
Gate threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 1mA	1.2	-	2.5	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{GS(th)}}{\Delta T_j}$	I_D = 1mA referenced to 25℃	-	-4.9	-	mV/℃
Static drain - source on - state resistance	$R_{DS(on)}$ *4	V_{GS} = 10V, I_D = 10A	-	11.0	14.3	mΩ
		V_{GS} = 4.5V, I_D = 10A	-	14.1	18.3	
Gate input resistance	R_G		-	2.3	-	Ω
Transconductance	g_{fs} *4	V_{DS} = 5V, I_D = 10A	7.5	-	-	S

*1 Pw ≦ 10μs, Duty cycle ≦ 1%

*2 L ≃ 0.2mH, V_{DD} = 20V, R_G = 25Ω, STARTING T_{ch} = 25℃ Fig.3-1,3-2

*3 MOUNTED ON A CERAMIC BOARD

*4 Pulsed

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●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C_{iss}	V_{GS} = 0V	-	615	-	pF
Output capacitance	C_{oss}	V_{DS} = 20V	-	100	-	
Reverse transfer capacitance	C_{rss}	f = 1MHz	-	28	-	
Turn - on delay time	$t_{d(on)}$ *4	V_{DD} ≃ 20V,V_{GS} = 10V	-	8.0	-	ns
Rise time	t_r *4	I_D = 5A	-	4.2	-	
Turn - off delay time	$t_{d(off)}$ *4	R_L = 4Ω	-	23.1	-	
Fall time	t_f *4	R_G = 10Ω	-	3.2	-	

●Gate charge characteristics (T_a = 25°C)

Parameter	Symbol	Conditions		Values			Unit
				Min.	Typ.	Max.	
Total gate charge	Q_g *4	V_{DD} ≃ 20V I_D = 10A	V_{GS} = 10V	-	8.4	-	nC
			V_{GS} = 4.5V	-	4.3	-	
Gate - Source charge	Q_{gs} *4			-	1.6	-	
Gate - Drain charge	Q_{gd} *4			-	1.2	-	

●Body diode electirical characteristics (Source-Drain) (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Body diode continuous forward current	I_S	T_a = 25℃	-	-	1.67	A
Body diode pulse current	I_{SP} *1		-	-	40	
Forward voltage	V_{SD} *4	V_{GS} = 0V, I_S = 1.67A	-	-	1.2	V
Reverse recovery time	t_{rr} *4	I_S = 10A, V_{GS}=0V di/dt = 100A/μs	-	21	-	ns
Reverse recovery charge	Q_{rr} *4		-	12	-	nC

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●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

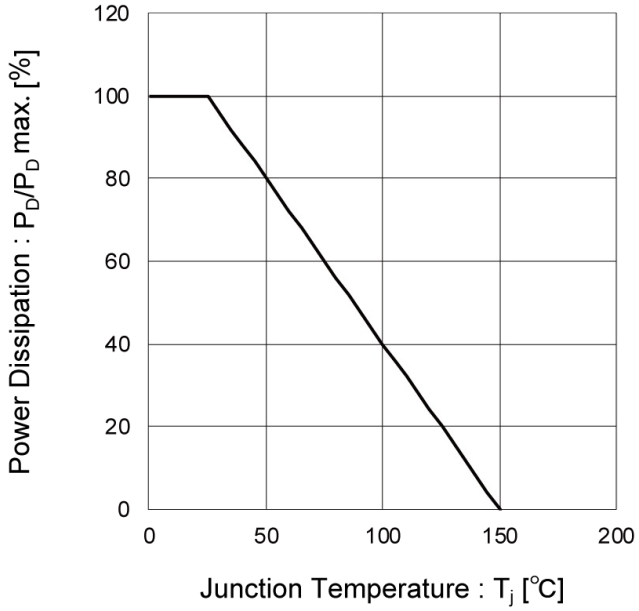


Fig.2 Maximum Safe Operating Area

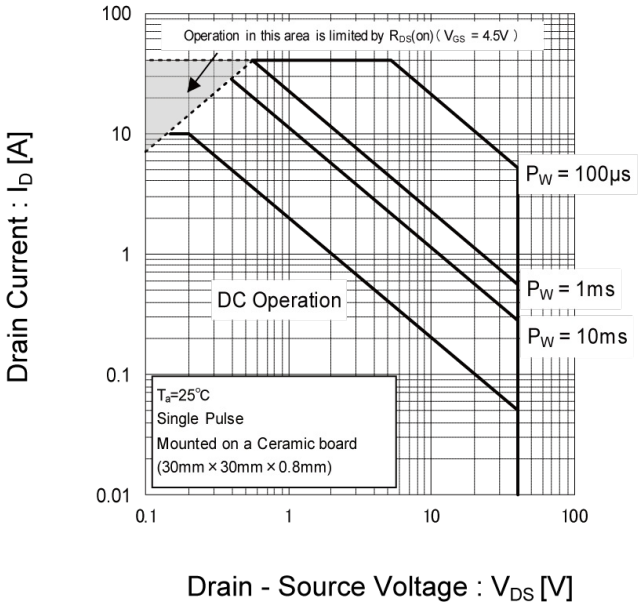


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

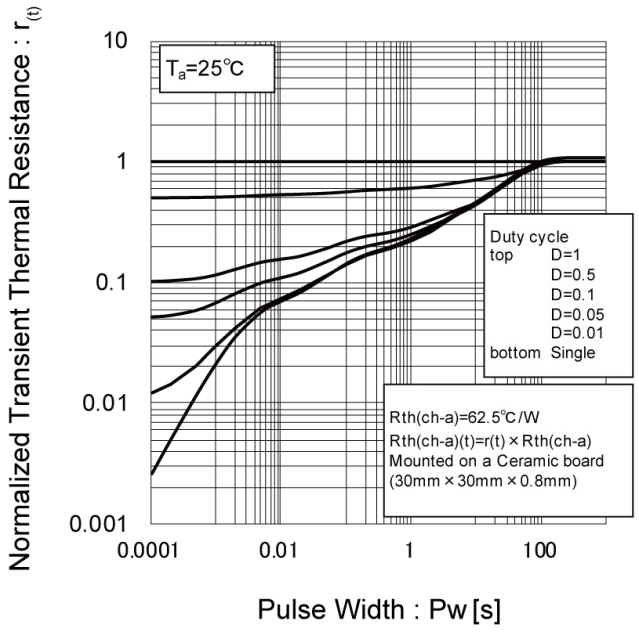
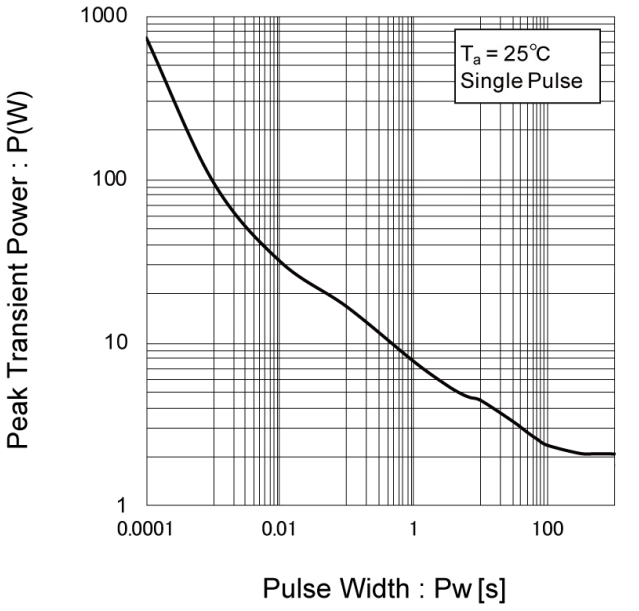


Fig.4 Single Pulse Maximum Power dissipation



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●Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)

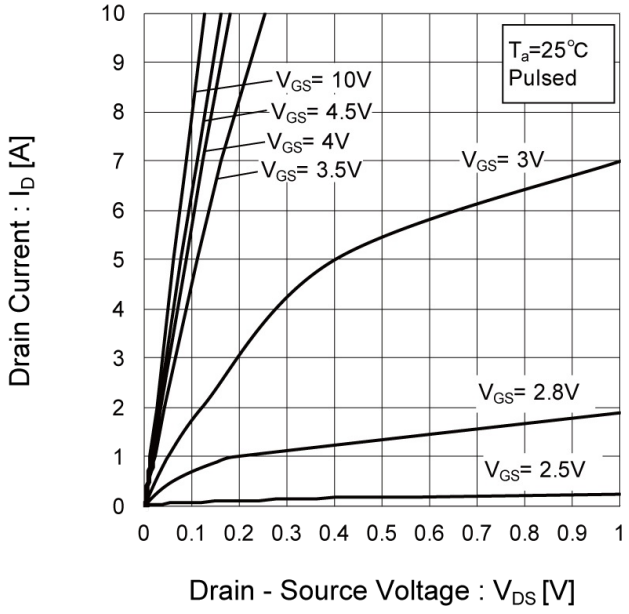


Fig.6 Typical Output Characteristics(II)

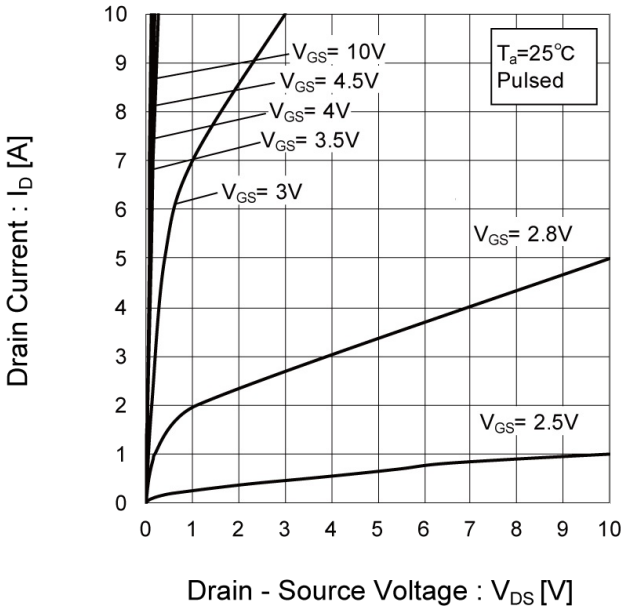
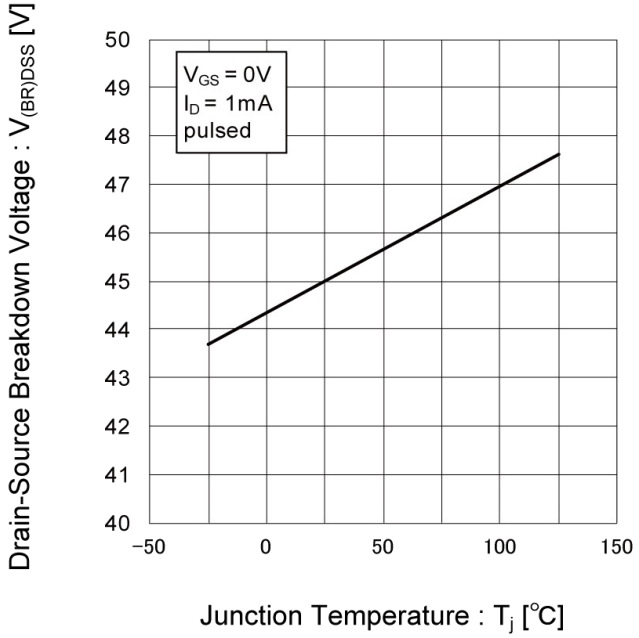


Fig.7 Breakdown Voltage vs. Junction Temperature



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●Electrical characteristic curves

Fig.8 Typical Transfer Characteristics

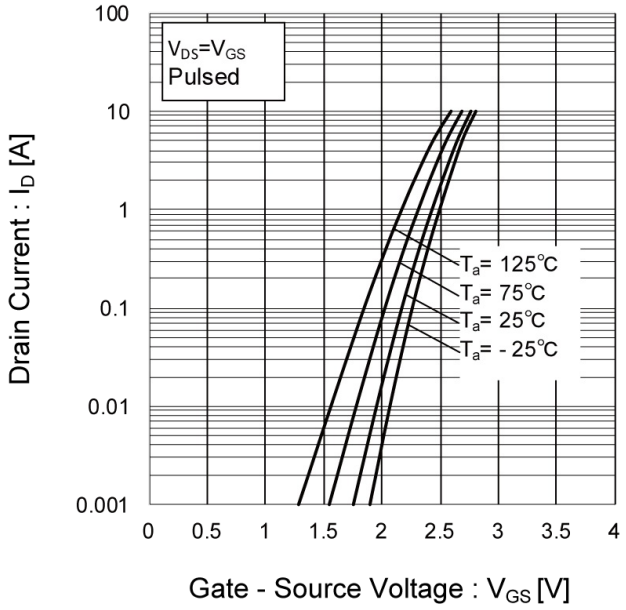


Fig.9 Gate Threshold Voltage vs. Junction Temperature

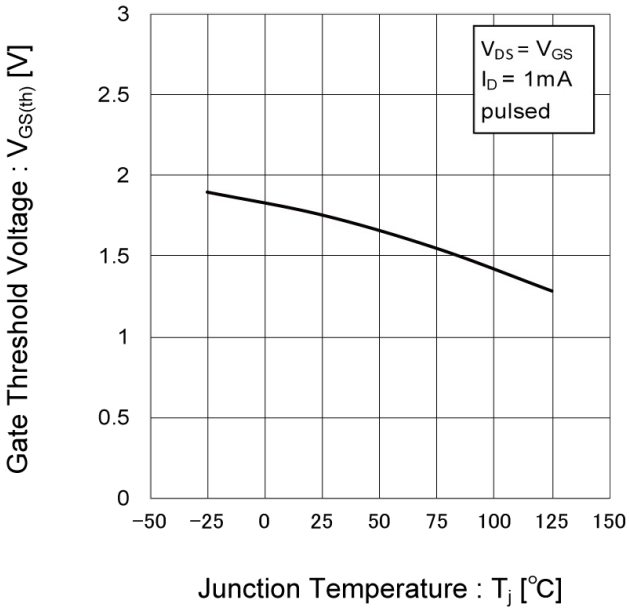
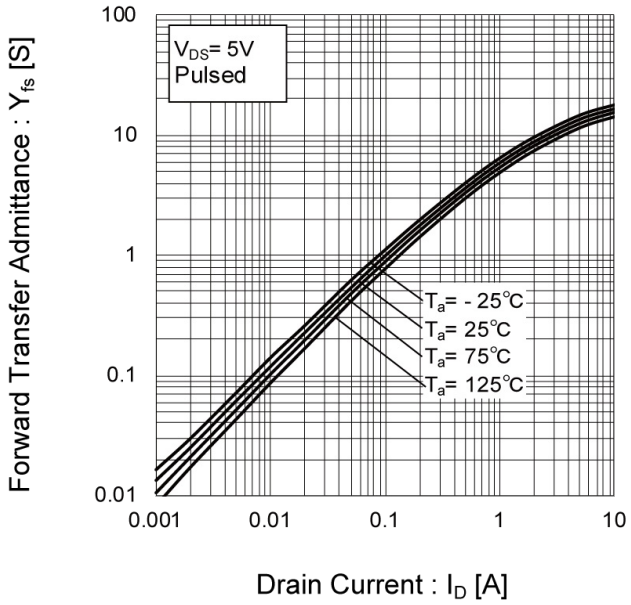


Fig.10 Transconductance vs. Drain Current



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●Electrical characteristic curves

Fig.11 Drain Current Derating Curve

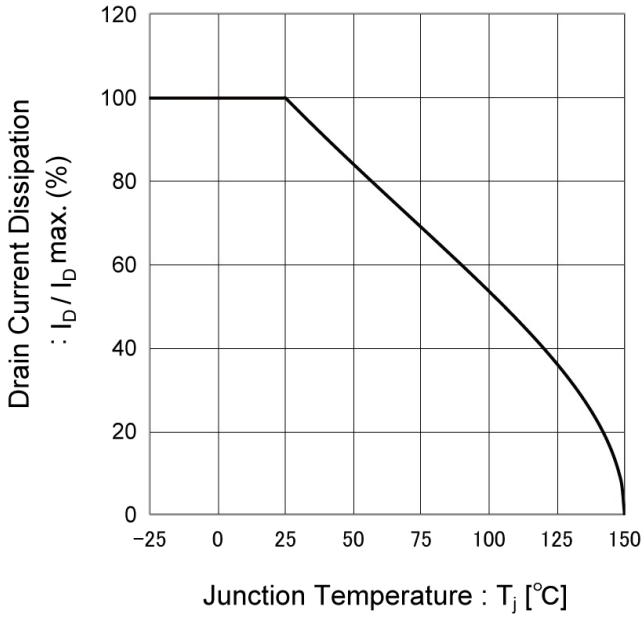


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

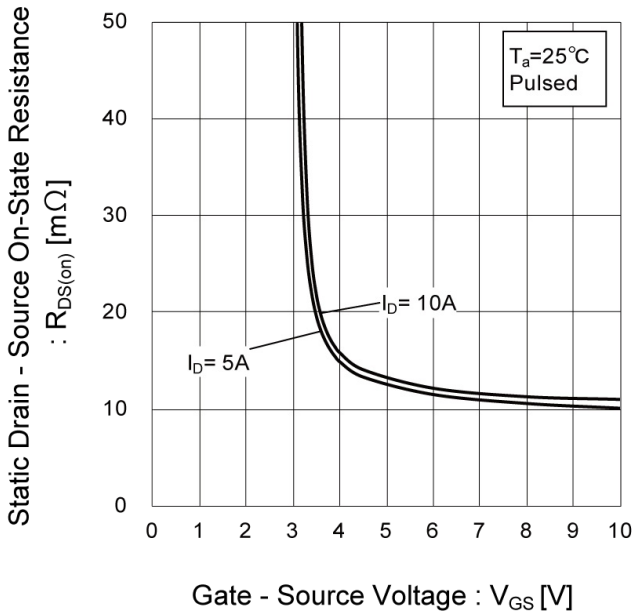
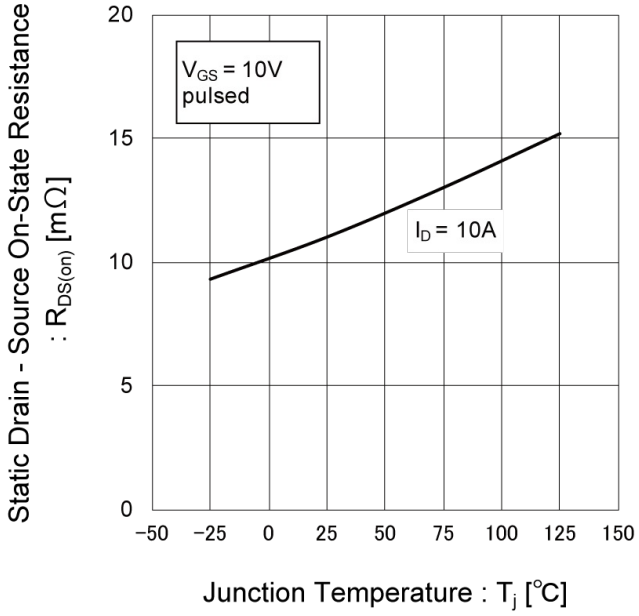


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature



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●Electrical characteristic curves

Fig.14 Static Drain - Source On - State Resistance vs. Drain Current(I)

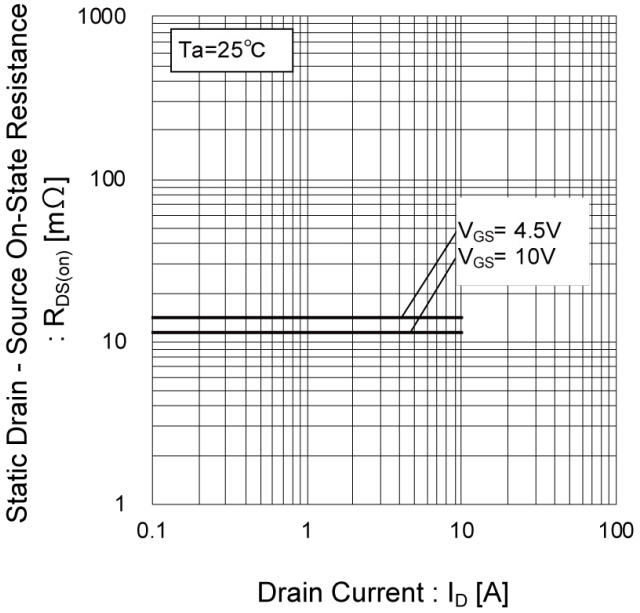


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)

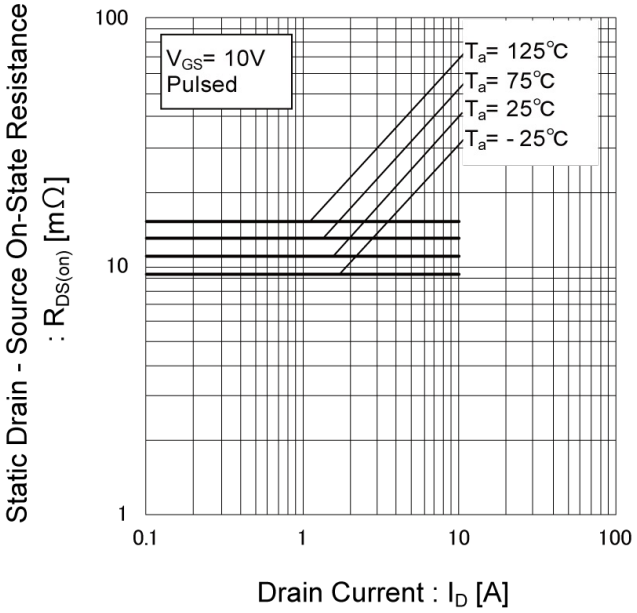
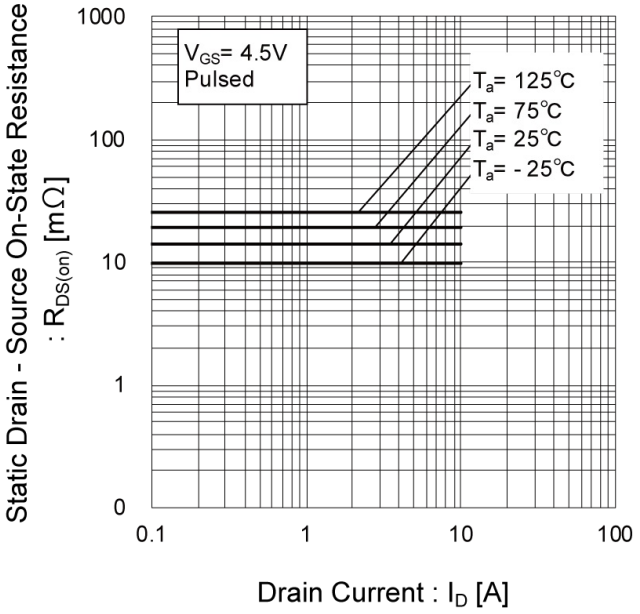


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current(III)



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●Electrical characteristic curves

Fig.17 Typical Capacitance vs. Drain - Source Voltage

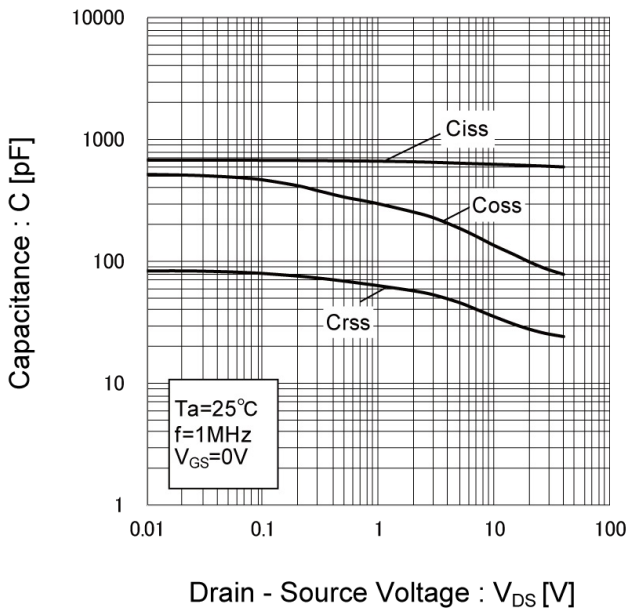


Fig.18 Switching Characteristics

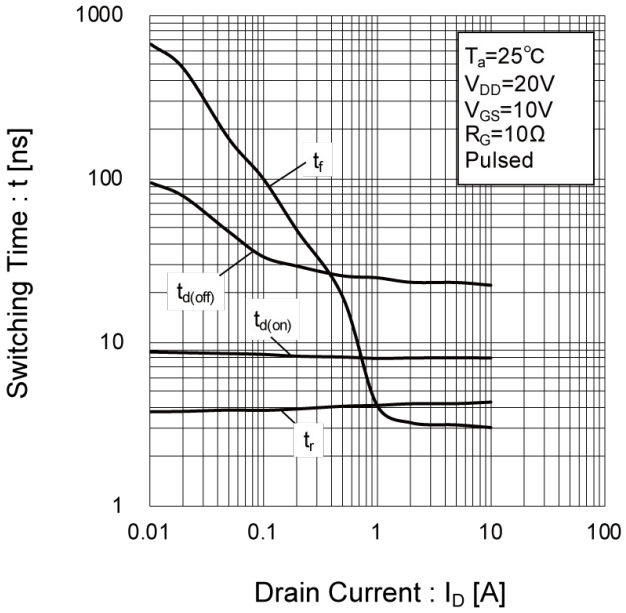


Fig.19 Dynamic Input Characteristics

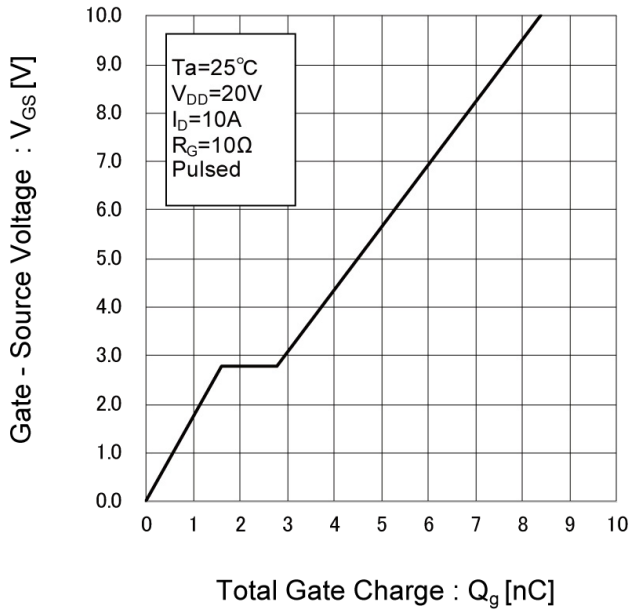
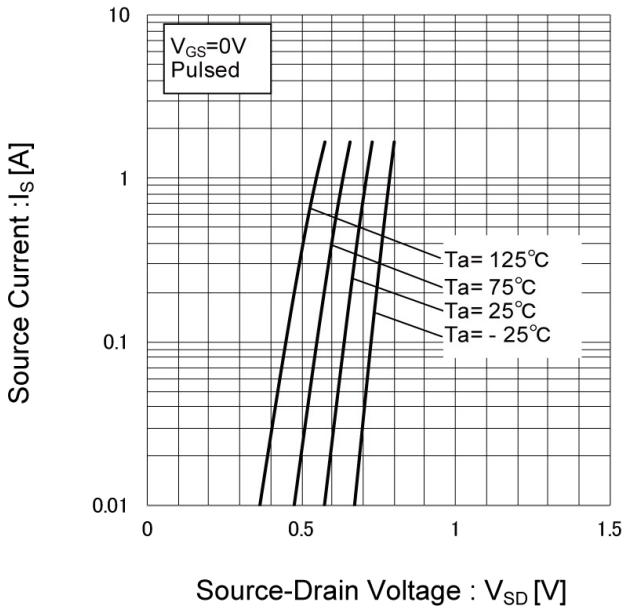


Fig.20 Source Current vs. Source Drain Voltage



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●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

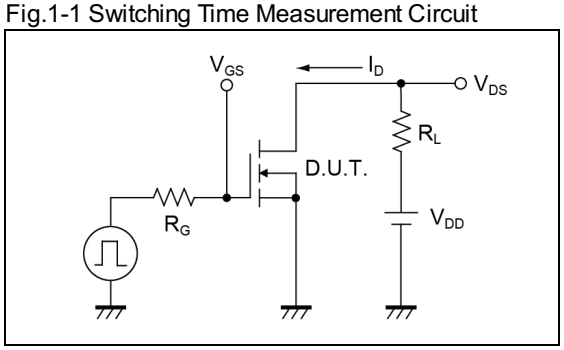


Fig.1-2 Switching Waveforms

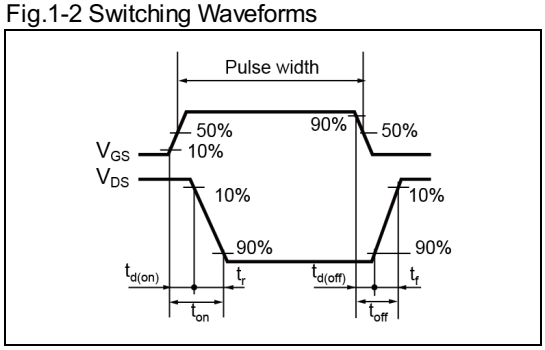


Fig.2-1 Gate Charge Measurement Circuit

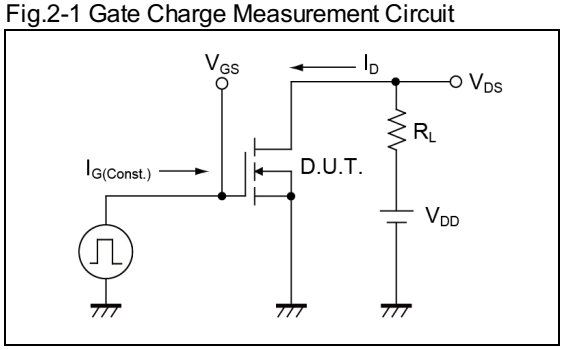


Fig.2-2 Gate Charge Waveform

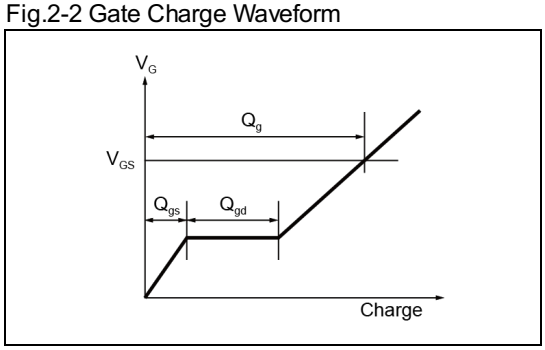


Fig.3-1 Avalanche Measurement Circuit

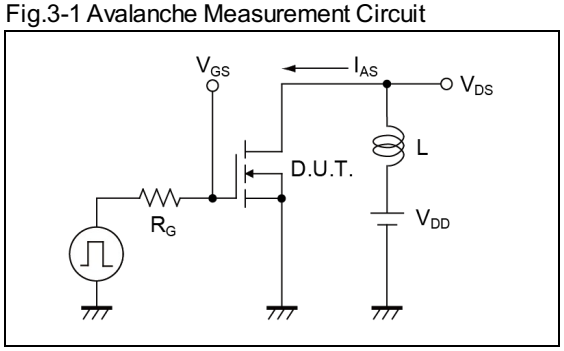
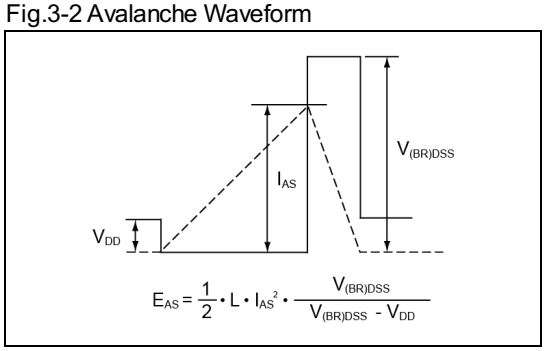


Fig.3-2 Avalanche Waveform



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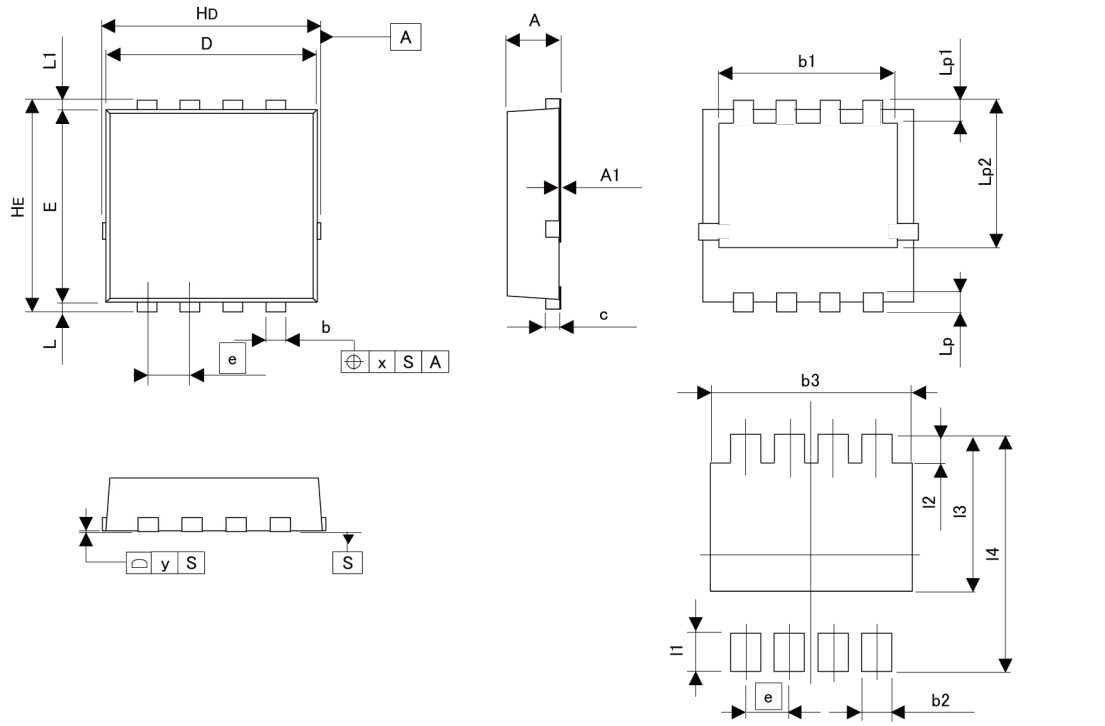
●Dimensions

HSMT8



Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.70	0.90	0.028	0.035
A1	0.00	0.05	0.000	0.002
b	0.27	0.37	0.011	0.015
b1	2.50	2.70	0.098	0.106
c	0.10	0.30	0.004	0.012
D	3.10	3.30	0.122	0.130
E	2.90	3.10	0.114	0.122
e	0.65		0.026	
HD	3.20	3.40	0.126	0.134
HE	3.20	3.40	0.126	0.134
L	0.07	0.25	0.003	0.010
L1	0.07	0.25	0.003	0.010
Lp	0.20	0.40	0.008	0.016
Lp1	0.25	0.45	0.010	0.018
Lp2	2.20	2.40	0.087	0.094
x	-	0.10	-	0.004
y	-	0.10	-	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	-	0.47	-	0.019
b3	-	2.70	-	0.106
l1	-	0.50	-	0.020
l2	-	0.55	-	0.022
l3	-	2.40	-	0.094
l4	-	3.40	-	0.134

Dimension in mm/inches

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Notes

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2) Before you use our Products, please contact our sales representative and verify the latest specifications :

3) Although ROHM is continuously working to improve product reliability and quality, semiconductors can break down and malfunction due to various factors.
Therefore, in order to prevent personal injury or fire arising from failure, please take safety measures such as complying with the derating characteristics, implementing redundant and fire prevention designs, and utilizing backups and fail-safe procedures. ROHM shall have no responsibility for any damages arising out of the use of our Poducts beyond the rating specified by ROHM.

4) Examples of application circuits, circuit constants and any other information contained herein are provided only to illustrate the standard usage and operations of the Products. The peripheral conditions must be taken into account when designing circuits for mass production.

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7) The Products specified in this document are not designed to be radiation tolerant.

8) For use of our Products in applications requiring a high degree of reliability (as exemplified below), please contact and consult with a ROHM representative : transportation equipment (i.e. cars, ships, trains), primary communication equipment, traffic lights, fire/crime prevention, safety equipment, medical systems, servers, solar cells, and power transmission systems.

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